



- 1 -

Docket No. 0756-1914

#26/E
9-27-03
Moush

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of) Art Unit: 2813
Shunpei YAMAZAKI et al.) Examiner: L. Schillinger
Serial No. 09/235,770)
Filed: January 25, 1999)
For: SEMICONDUCTOR DEVICE)
AND METHOD FOR FORMING)
THE SAME)

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with
The United States Postal Service with sufficient postage as First
Class Mail in an envelope addressed to: Commissioner for Patents,
Washington, D.C. 20231, on 2-6-2003
Adele M. Stamper
Adele M. Stamper

SUPPLEMENTAL AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

Further to the Amendment filed November 4, 2002, please amend the above-
identified application as follows:

IN THE CLAIMS:

Please amend claim 4 as follows:

RECEIVED
FEB 14 2003
TECHNOLOGY CENTER 28000

4. (Amended) A semiconductor device comprising:
- a first insulating film comprising silicon nitride formed on a substrate;
 - a second insulating film comprising silicon oxide formed on said first insulating film;
 - a semiconductor layer formed on said second insulating film wherein said semiconductor layer includes at least source, drain and channel regions;
 - a third insulating film comprising silicon oxide formed on said semiconductor layer wherein said third insulating film extends beyond edges of said semiconductor layer so that said second and third insulating films are in direct contact to each other;

48

E